

Features

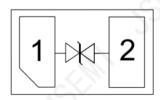
- ◆ 30W (8/20 µs) Peak Pulse Power
- ◆ Low Capacitance ESD Protection
- ◆ DFN1006-2 Package
- ◆ RoHS Compliant
- ◆ Matte Tin Lead finish (Pb-Free)
- ◆ Protect One High Speed Data Line
- ◆ Meet IEC61000-4-2 Level 4: Contact Discharge > 8kV Air Discharge > 15kV



Circuit Diagram

Applications

- ◆ Communication System
- ◆ Portable Instrumentation
- ◆ Audio and Video Equipment
- ◆ Computers and Peripherals
- ◆ USB 1.1, USB 2.0 Ports



Package Outline

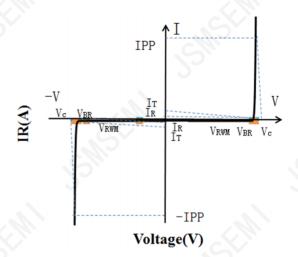
Maximum Ratings (Ta = 25℃)

Symbol	Parameter	Value	Unit
РРК	Peak Pulse Power	30	W
IPP	Peak Pulse Current	2	A
VESD (Contact)	Contact ESD Voltage per IEC61000-4-2	15	kV
VESD (Air)	Air ESD Voltage per IEC61000-4-2	15	kV
TJ	Junction Temperature	-55 to +150	င
TSTG	Storage Temperature	-55 to +150	°C C
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Portion Electronics Parameter

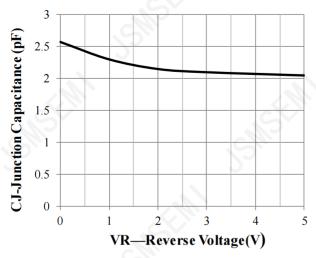
Symbol	Parameter		
Іт	Test Current		
Ірр	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @Ic		



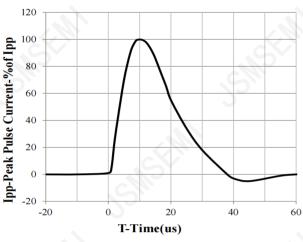
Electrical Characteristics (Ta = 25℃)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VRWM	Reverse Working Peak Voltage				5	V
VBR	Reverse Breakdown Voltage	IT = 1mA	6.0		9	V
IR	Reverse Leakage Current	VRWM = 5V			0.2	μA
VC	Clamping Voltage	IPP = 1A (8/20μs)			12	V
VC	Clamping Voltage	IPP = 2A (8/20 μs)			15	V
CJ	Capacitance	VR = 0V, f = 1MHz	cill	2.5	3.5	pF

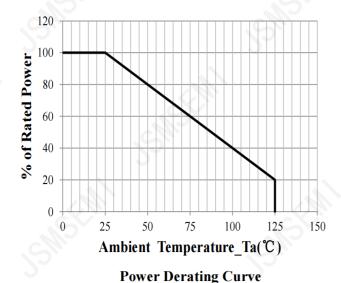
Typical Performance Curves



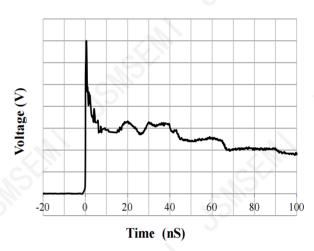
Junction Capacitance vs. Reverse Voltage



8 X 20us Pulse Waveform



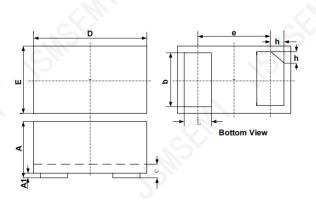
Clamping Voltage vs. Peak Pulse Current



IEC61000-4-2 Pulse Waveform

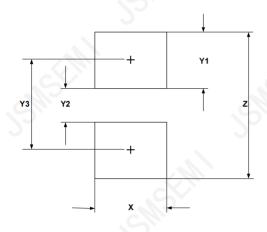


DFN1006-2(0402)Package Outline Drawing



		DIMENSIONS					
	MI	MILLIMETERS			INCHES		
SYM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.45	0.50	0.55	0.018	0.020	0.022	
A1	0.00	0.02	0.05	0.000	0.001	0.002	
b	0.45	0.50	0.55	0.018	0.020	0.022	
С	0.12	0.15	0.18	0.005	0.006	0.007	
D	0.95	1.00	1.05	0.037	0.039	0.041	
е	0.65 BSC		C	.026 BS	2		
Е	0.55	0.60	0.65	0.022	0.024	0.026	
L	0.20	0.25	0.30	0.008	0.010	0.012	
h	0.07	0.12	0.17	0.003	0.005	0.007	

Suggested Land Pattern



SYM	DIMENSIONS			
STIVI	MILLIMETERS	INCHES		
X	0.60	0.024		
Y1	0.50	0.020		
Y2	0.30	0.012		
Y3	0.80	0.032		
Z	1.30	0.052		



Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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